



RECTRON

SEMICONDUCTOR

TECHNICAL SPECIFICATION

1N914B

1N914B SIGNAL DIODE

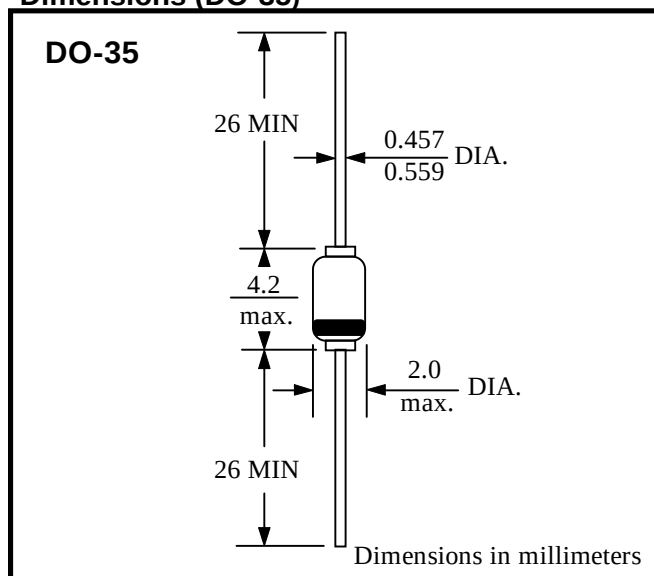
Absolute Maximum Ratings (Ta=25°C)

Items	Symbol	Ratings	Unit
Reverse Voltage	VR	75	V
Reverse Recovery Time	trr	4	ns
Power Dissipation 3.33mW/°C (25°C)	P	500	mW
Forward Current	IF	300	mA
Junction Temp.	Tj	-65 to 175	°C
Storage Temp.	Tstg	-65 to 175	°C

Mechanical Data

Items	Materials
Package	DO-35
Case	Hermetically sealed glass
Chip	Glass Passivated

Dimensions (DO-35)



Electrical Characteristics (Ta=25°C)

Ratings	Symbol	Ratings	Unit
Minimum Breakdown Voltage IR= 5.0uA IR= 100uA	BV	75 100	V
Peak Forward Surge Current PW= 1sec.	IFsurge	0.5	A
Maximum Forward Voltage IF= 100mA	VF	1.0	V
Maximum Reverse Current VR= 20V VR= 75V VR= 20V, Tj= 150°C	IR	0.025 5.0 50	uA
Maximum Junction Capacitance VR= 0, f= 1 MHz	Cj	4	pF
Maximum Reverse Recovery Time IF= 10mA, VR= 6V, IRR= 1mA, RL= 100Ω	trr	4	ns